Central™
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Manufacturers of World Class Discrete Semiconductors

2N5366
2N5367

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5366, 2N5367 types are PNP Silicon Planar Epitaxial Transistors designed for general purpose switching and amplifier applications.

MAXIMUM RATINGS ($T_A = 25^oC$)

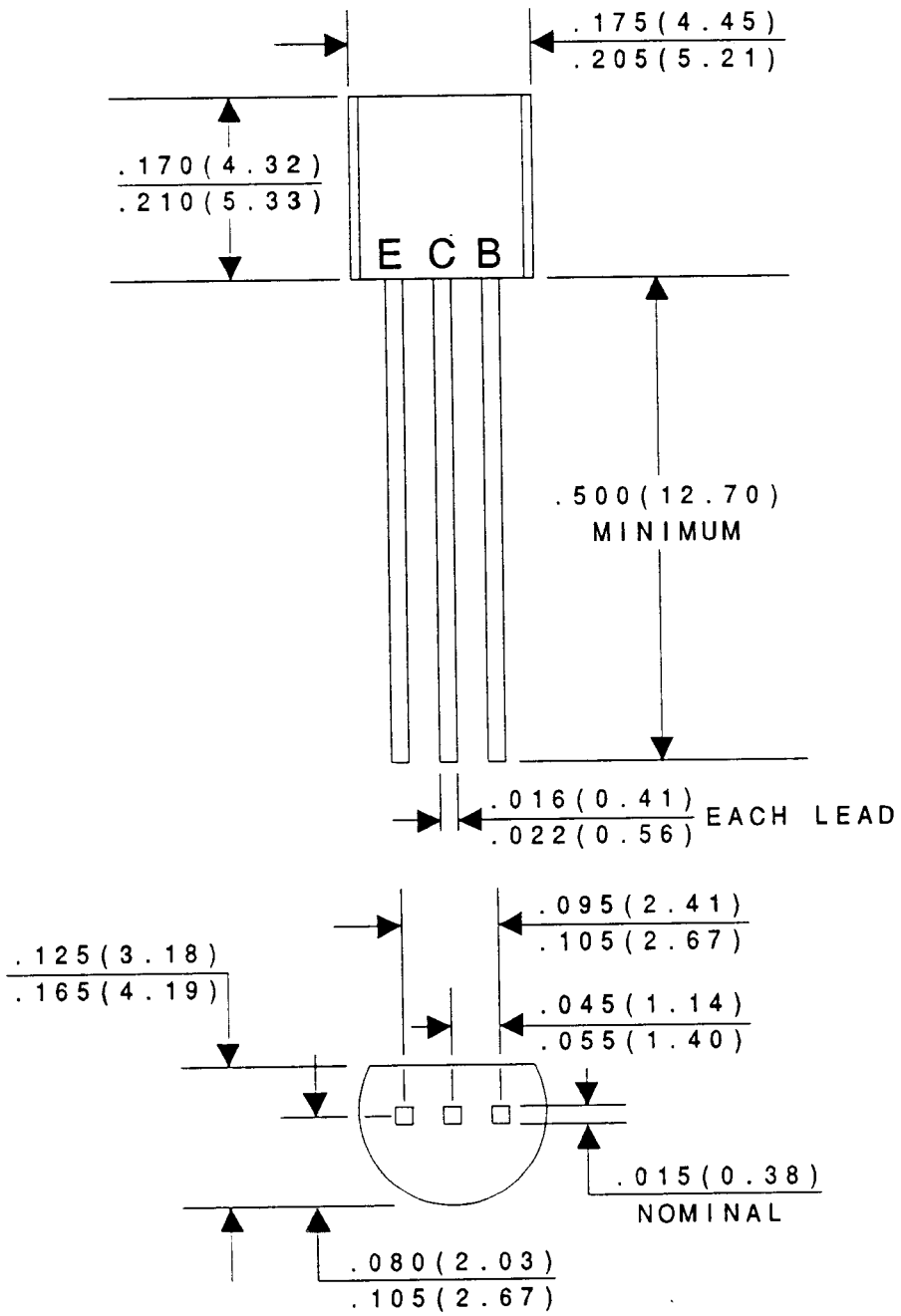
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Continuous Collector Current	I_C	300	mA
Collector Current (t = 10μsec)	I_C	700	mA
Power Dissipation	P_D	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	^oC
Thermal Resistance	Θ_{JA}	0.2	$^oC/mW$

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

		2N5366		2N5367		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
I_{CBO}	$V_{CB} = 40V$		100		100	nA
I_{CBO}	$V_{CB} = 40V$, $T_A = 100^oC$		10		10	μA
I_{CES}	$V_{CB} = 40V$		100		100	nA
I_{EBO}	$V_{EB} = 4.0V$		10		10	μA
BV_{CEO}	$I_C = 10mA$	40		40		V
$V_{CE(SAT)}$	$I_C = 50mA$, $I_B = 2.5mA$		0.25		0.25	V
$V_{CE(SAT)}$	$I_C = 300mA$, $I_B = 30mA$		1.0		1.0	V
$V_{BE(SAT)}$	$I_C = 50mA$, $I_B = 2.5mA$		1.1		1.1	V
$V_{BE(SAT)}$	$I_C = 300mA$, $I_B = 30mA$		2.0		2.0	V
$V_{BE(ON)}$	$V_{CE} = 10V$, $I_C = 2.0mA$	0.5	0.8	0.5	0.8	V
h_{FE}	$V_{CE} = 10V$, $I_C = 2.0mA$	80		200		
h_{FE}	$V_{CE} = 1.0V$, $I_C = 50mA$	100	300	250	500	
h_{FE}	$V_{CE} = 5.0V$, $I_C = 300mA$	40		75		
C_{ob}	$V_{CB} = 10V$, $I_E = 0$, f = 1.0MHz		8.0		8.0	pF
C_{ib}	$V_{EB} = 0.5V$, $I_C = 0$, f = 1.0MHz		35		35	pF
h_{fe}	$V_{CE} = 10V$, $I_C = 2.0mA$, f = 1.0kHz	80	450	200	750	
f_T	$V_{CE} = 10V$, $I_C = 2.0mA$	250 TYP		250 TYP		MHz

(OVER)

JEDEC TO-92 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

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